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Nota di contenuto	<p>Nitride Semiconductors Handbook on Materials and Devices; Contents; Preface; List of Contributors; Part 1 Material; 1 High-Pressure Crystallization of GaN; 1.1 Introduction; 1.2 High-Pressure Crystallization of GaN; 1.2.1 Thermodynamics - Properties of GaN-GaN(2) System; 1.2.2 Dissolution Kinetics of N(2) and Crystal Growth Mechanism; 1.2.3 What Happens with GaN at High Temperature when the N(2) Pressure is too Low?; 1.2.4 Crystallization of GaN Using High Nitrogen Pressure Solution Growth (HNPSG) Method - Experimental; 1.2.5 Properties of GaN Single Crystals Obtained by HNPSG Method 1.2.5.1 Crystals Grown without Intentional Seeding 1.2.5.2 Seeded Growth of GaN by HNPS Method; 1.2.6 Physical Properties of GaN Crystals, Grown by HNPS Method; 1.2.6.1 Point Defects; 1.2.6.2 Extended Defects; 1.3 Epitaxy on Bulk GaN; 1.3.1 Introduction; 1.3.2 Metalorganic Chemical Vapor Epitaxy on GaN Substrates in HPRC Unipress; 1.3.3 Molecular Beam Epitaxy; 1.4 Optoelectronic Devices; 1.4.1 Introduction; 1.4.2 Light Emitting Diodes Fabricated on Bulk GaN in HPRC; 1.4.3 Laser Diode Structures; 1.5 Conclusions; 1.6 Acknowledgment; 1.7 References; 2 Epitaxial Lateral Overgrowth of GaN          2.1 Heteroepitaxial GaN 2.1.1 Introduction; 2.1.2 Growth of GaN/Sapphire and 6H-SiC Templates; 2.1.2.1 2D Growth Mode (GaN/Sapphire); 2.1.2.2 3D Growth Mode (GaN/Sapphire); 2.1.3 Defects in GaN/Sapphire and GaN/6H-SiC; 2.1.3.1 Extended Defects; 2.1.3.2 Native Defects; 2.1.3.3 Defect-Related Optical Properties; 2.1.3.4 Device Performance Limitations; 2.1.3.5 Electronic Properties of Defects; 2.2 Epitaxial Lateral Overgrowth (ELO); 2.2.1 Standard ELO; 2.2.2 Rationale; 2.2.3 Experimental; 2.3 One-Step Lateral Overgrowth (1S-ELO); 2.3.1 ELO in MOVPE; 2.3.1.1 Morphology and Defects 2.3.1.2 Structural Assessment 2.3.1.3 Kinetics; 2.3.1.4 In-Depth Optical Assessment of MOVPE ELO GaN; 2.3.2 HVPE; 2.3.2.1 In-Depth Assessment of HVPE ELO GaN; 2.3.2.2 Stripe Openings along ; 2.3.2.3 Selective Area Epitaxy (SAE); 2.3.2.4 (C(2)H(5))(2)GaCl as Ga Source; 2.3.2.5 Stress Generation; 2.3.3 Sublimation; 2.3.4 New Developments; 2.3.4.1 ELO on Si; 2.3.4.2 Using W as Mask; 2.3.4.3 Maskless ELO; 2.3.5 Improvements of the Standard ELO Method; 2.3.6 Pendo-Epitaxy; 2.3.7 ELO of Cubic GaN; 2.4 Two-Step ELO (2S-ELO); 2.4.1 Experimental (MOVPE); 2.4.2 In-Depth Assessment of 2S-ELO 2.4.2.1 Cathodoluminescence 2.4.2.2 Luminescence of GaN by Epitaxial Lateral Overgrowth; 2.4.2.3 Time-resolved Photoluminescence; 2.4.2.4 Deep Level Transient Spectroscopy (DLTS); 2.4.2.5 Strain Distribution; 2.4.3 Assessment of HVPE; 2.4.4 ELO and Yellow Luminescence; 2.4.5 Conclusion; 2.5 New Trends; 2.5.1 3S-ELO; 2.5.2 Further Improvements; 2.6 Theoretical Analysis of ELO; 2.7 Acknowledgments; 2.8 References; 3 Plasma-Assisted Molecular Beam Epitaxy of III-V Nitrides; 3.1 Introduction; 3.2 The Nitrogen Plasma Source; 3.2.1 The Different Sources; 3.2.2 The Nitrogen Plasma 3.2.3 Characterization of the HD25 RF Source by Optical Emission Spectroscopy</p>
Sommario/riassunto	Semiconductor components based on silicon have been used in a wide range of applications for some time now. These elemental semiconductors are now well researched and technologically well developed. In the meantime the focus has switched to a new group of materials: ceramic semiconductors based on nitrides are currently the subject of research due to their optical and electronic characteristics. They open up new industrial possibilities in the field of photosensors,

as light sources or as electronic components. This collection of review articles provides a systematic and in-depth overview o